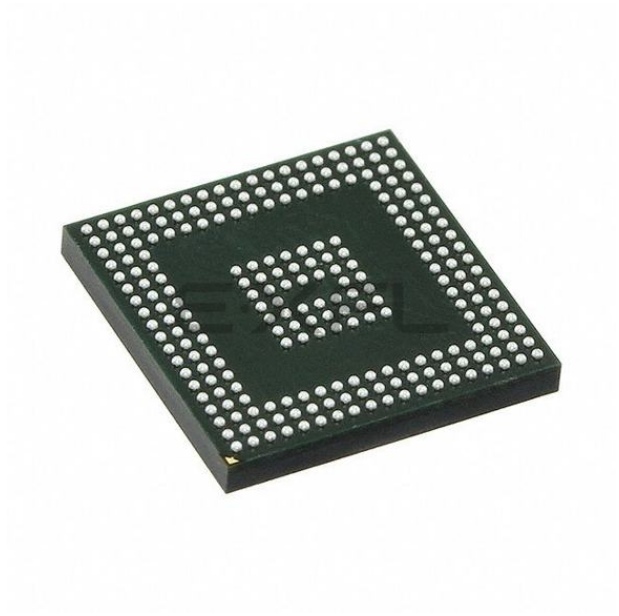
AMD Xilinx - XC7A12T-1CPG236I Datasheet



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Details	
Product Status	Obsolete
Number of LABs/CLBs	1000
Number of Logic Elements/Cells	12800
Total RAM Bits	737280
Number of I/O	106
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	238-LFBGA, CSPBGA
Supplier Device Package	238-CSBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7a12t-1cpg236i

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies (6)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies (6)	–	+260	°C
T_j	Maximum junction temperature(6)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to UG471: *7 Series FPGAs SelectIO Resources User Guide*.
4. The maximum limit applied to DC signals.
5. For maximum undershoot and overshoot AC specifications, see Table 4.
6. For soldering guidelines and thermal considerations, see UG475: *7 Series FPGA Packaging and Pinout Specification*.

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}	Internal supply voltage	0.95	1.00	1.05	V
	For -2L (0.9V) devices: internal supply voltage	0.87	0.90	0.93	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCBRAM}	Block RAM supply voltage	0.95	1.00	1.05	V
V_{CCO}(3)(4)	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
V_{IN}(5)	I/O input voltage	–0.20	–	V_{CCO} + 0.20	V
	I/O input voltage for V_{REF} and differential I/O standards	–0.20	–	2.625	V
I_{IN}(6)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}(7)	Battery voltage	1.0	–	1.89	V
GTP Transceiver					
$V_{MGTAVCC}$(8)(9)	Analog supply voltage for the GTP transmitter and receiver circuits	0.97	1.0	1.03	V
$V_{MGTAVTT}$(8)(9)	Analog supply voltage for the GTP transmitter and receiver termination circuits	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V

Table 2: **Recommended Operating Conditions(1)(2) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. For the design of the power distribution system consult UG483, *7 Series FPGAs PCB Design and Pin Planning Guide*.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG482: *7 Series FPGAs GTP Transceiver User Guide*.
9. Voltages are specified for the temperature range of T_j = 0°C to +85°C.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}(2)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}(3)	Battery supply current	–	–	150	nA
R_{IN_TERM}(4)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40) for commercial (C), and industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50) for commercial (C), and industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60) for commercial (C), and industrial (I), and extended (E) temperature devices	44	60	83	Ω

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[1]	Max	Units
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a $V_{CCO}/2$ level.

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks[1]**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.40	100	–0.40	100
V_{CCO} + 0.45	100	–0.45	61.7
V_{CCO} + 0.50	100	–0.50	25.8
V_{CCO} + 0.55	100	–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7A100T	155	155	155	108	mA
		XC7A200T	328	328	328	232	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7A100T	4	4	4	4	mA
		XC7A200T	5	5	5	5	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7A100T	36	36	36	36	mA
		XC7A200T	73	73	73	73	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7A100T	4	4	4	4	mA
		XC7A200T	11	11	11	11	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperature (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTP transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 6 shows the minimum current, in addition to I_{CCQ}, that is required by Artix-7 devices for proper power-on and configuration. If the current minimums shown in Table 5 and Table 6 are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 6: **Power-On Current for Artix-7 Devices(1)**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
	Typ(2)	Typ(2)	Typ(2)	Typ(2)	
XC7A100T	I_{CCINTQ} + 170	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7A200T	I_{CCINTQ} + 340	I_{CCAUXQ} + 50	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 80	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.
2. Typical values are specified at nominal voltage, 25°C.

Table 7: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100°C$(1)	–	500	ms
		$T_J = 85°C$(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels(1)(2)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 3	Note 3
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 5	Note 5
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.500	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. For detailed interface specific DC voltage levels, see UG471: *7 Series FPGAs SelectIO Resources User Guide*.

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Artix-7 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the AC Switching Characteristics, page 9.

Table 14: **Networking Applications Interface Performances**

Description	Speed Grade				Units
	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	680	680	600	600	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	1250	1250	950	950	Mb/s
SDR LVDS receiver (SFI-4.1)(1)	680	680	600	600	Mb/s
DDR LVDS receiver (SPI-4.2)(1)	1250	1250	950	950	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 15: **Maximum Physical Interface (PHY) Rate for Memory Interfaces(1)(2)**

Memory Standard	Speed Grade				Units
	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	
4:1 Memory Controllers					
DDR3	1066	800	800	800	Mb/s
DDR3L	800	800	667	667	Mb/s
DDR2	800	800	667	667	Mb/s
LPDDR2	667	667	533	533	Mb/s
2:1 Memory Controllers					
DDR3	800	700	620	620	Mb/s
DDR3L	800	700	620	620	Mb/s
DDR2	800	700	620	620	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see UG586, *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).

IOB Pad Input/Output/3-State

Table 16 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 16: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVTTL_S4	1.26	1.34	1.41	1.58	3.80	3.93	4.18	4.41	4.37	4.59	5.01	5.06	ns
LVTTL_S8	1.26	1.34	1.41	1.58	3.54	3.66	3.92	4.15	4.11	4.32	4.75	4.80	ns
LVTTL_S12	1.26	1.34	1.41	1.58	3.52	3.65	3.90	4.13	4.09	4.31	4.73	4.78	ns
LVTTL_S16	1.26	1.34	1.41	1.58	3.07	3.19	3.45	3.68	3.64	3.85	4.28	4.33	ns
LVTTL_S24	1.26	1.34	1.41	1.58	3.29	3.41	3.67	3.90	3.86	4.07	4.50	4.55	ns
LVTTL_F4	1.26	1.34	1.41	1.58	3.26	3.38	3.64	3.86	3.83	4.04	4.46	4.51	ns
LVTTL_F8	1.26	1.34	1.41	1.58	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns
LVTTL_F12	1.26	1.34	1.41	1.58	2.73	2.85	3.10	3.33	3.29	3.51	3.93	3.98	ns
LVTTL_F16	1.26	1.34	1.41	1.58	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns
LVTTL_F24	1.26	1.34	1.41	1.58	2.52	2.65	2.90	3.22	3.09	3.31	3.73	3.87	ns
LVDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns
MINI_LVDS_25	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns
BLVDS_25	0.73	0.81	0.88	0.90	1.84	1.96	2.21	2.44	2.40	2.62	3.04	3.09	ns
RSDS_25 (point to point)	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns
PPDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.88	1.86	2.07	2.49	2.53	ns
TMDS_33	0.73	0.81	0.88	0.90	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns
PCI33_3	1.24	1.32	1.39	1.57	3.10	3.22	3.48	3.71	3.67	3.88	4.31	4.36	ns
HSUL_12	0.67	0.75	0.82	0.87	1.80	1.93	2.18	2.41	2.37	2.59	3.01	3.06	ns
DIFF_HSUL_12	0.68	0.76	0.83	0.88	1.80	1.93	2.18	2.21	2.37	2.59	3.01	2.86	ns
HSTL_I_S	0.67	0.75	0.82	0.87	1.62	1.74	1.99	2.19	2.19	2.40	2.82	2.84	ns
HSTL_II_S	0.65	0.73	0.80	0.85	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns
HSTL_I_18_S	0.67	0.75	0.82	0.87	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns
HSTL_II_18_S	0.66	0.75	0.81	0.87	1.41	1.54	1.79	1.97	1.98	2.20	2.62	2.62	ns
DIFF_HSTL_I_S	0.68	0.76	0.83	0.85	1.59	1.71	1.96	2.13	2.15	2.37	2.79	2.78	ns
DIFF_HSTL_II_S	0.68	0.76	0.83	0.85	1.51	1.63	1.88	2.07	2.08	2.29	2.71	2.72	ns
DIFF_HSTL_I_18_S	0.71	0.79	0.86	0.87	1.38	1.51	1.76	1.96	1.95	2.17	2.59	2.61	ns
DIFF_HSTL_II_18_S	0.70	0.78	0.85	0.87	1.46	1.58	1.84	2.00	2.03	2.24	2.67	2.65	ns
HSTL_I_F	0.67	0.75	0.82	0.87	1.10	1.22	1.48	1.69	1.67	1.88	2.31	2.34	ns

Input/Output Logic Switching Characteristics

Table 18: **ILOGIC Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T_{ICE1CK}/T_{ICKCE1}	CE1 pin setup/hold with respect to CLK	0.48/0.02	0.54/0.02	0.76/0.02	0.40/–0.07	ns
T_{ISRCK}/T_{ICKSR}	SR pin setup/hold with respect to CLK	0.60/0.01	0.70/0.01	1.13/0.01	0.88/–0.35	ns
T_{IDOCK}/T_{IOCKD}	D pin setup/hold with respect to CLK without Delay	0.01/0.27	0.01/0.29	0.01/0.33	0.01/0.33	ns
T_{IDOCKD}/T_{IOCKDD}	DDLY pin setup/hold with respect to CLK (using IDELAY)	0.02/0.27	0.02/0.29	0.02/0.33	0.01/0.33	ns
Combinatorial						
T_{IDI}	D pin to O pin propagation delay, no Delay	0.11	0.11	0.13	0.14	ns
T_{IDID}	DDLY pin to O pin propagation delay (using IDELAY)	0.11	0.12	0.14	0.15	ns
Sequential Delays						
T_{IDLO}	D pin to Q1 pin using flip-flop as a latch without Delay	0.41	0.44	0.51	0.54	ns
T_{IDLOD}	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY)	0.41	0.44	0.51	0.55	ns
T_{ICKQ}	CLK to Q outputs	0.53	0.57	0.66	0.71	ns
T_{RQ_ILOGIC}	SR pin to OQ/TQ out	0.96	1.08	1.32	1.32	ns
T_{GSRQ_ILOGIC}	Global set/reset to Q outputs	7.60	7.60	10.51	11.39	ns
Set/Reset						
T_{RPW_ILOGIC}	Minimum pulse width, SR inputs	0.61	0.72	0.72	0.68	ns, Min

Table 19: **OLOGIC Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T_{ODCK}/T_{OCKD}	D1/D2 pins setup/hold with respect to CLK	0.67/–0.11	0.71/–0.11	0.84/–0.11	0.60/–0.18	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin setup/hold with respect to CLK	0.32/0.58	0.34/0.58	0.51/0.58	0.21/–0.10	ns
T_{OSRCK}/T_{OCKSR}	SR pin setup/hold with respect to CLK	0.37/0.21	0.44/0.21	0.80/0.21	0.62/–0.25	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins setup/hold with respect to CLK	0.69/–0.14	0.73/–0.14	0.89/–0.14	0.60/–0.18	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin setup/hold with respect to CLK	0.32/0.01	0.34/0.01	0.51/0.01	0.22/–0.10	ns
Combinatorial						
T_{ODQ}	D1 to OQ out or T1 to TQ out	0.83	0.96	1.16	1.36	ns
Sequential Delays						
T_{OCKQ}	CLK to OQ/TQ out	0.47	0.49	0.56	0.63	ns
T_{RQ_OLOGIC}	SR pin to OQ/TQ out	0.72	0.80	0.95	1.12	ns
T_{GSRQ_OLOGIC}	Global set/reset to Q outputs	7.60	7.60	10.51	11.39	ns
Set/Reset						
T_{RPW_OLOGIC}	Minimum pulse width, SR inputs	0.64	0.74	0.74	0.68	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 20: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold for Control Lines						
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV	0.01/0.14	0.02/0.15	0.02/0.17	0.02/0.21	ns
T_{ISCCK_CE} / T_{ISCKC_CE}(2)	CE pin setup/hold with respect to CLK (for CE1)	0.45/–0.01	0.50/–0.01	0.72/–0.01	0.35/–0.11	ns
T_{ISCCK_CE2} / T_{ISCKC_CE2}(2)	CE pin setup/hold with respect to CLKDIV (for CE2)	–0.10/0.33	–0.10/0.36	–0.10/0.40	–0.17/0.40	ns
Setup/Hold for Data Lines						
T_{ISDCK_D} /T_{ISCKD_D}	D pin setup/hold with respect to CLK	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.04/0.19	ns
T_{ISDCK_DDLY} /T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY)(1)	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.03/0.19	ns
$T_{ISDCK\_D\_DDR}$ /$T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.04/0.19	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY)(1)	0.12/0.12	0.14/0.14	0.17/0.17	0.19/0.19	ns
Sequential Delays						
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.53	0.54	0.66	0.67	ns
Propagation Delays						
T_{ISDO_DO}	D input to DO output pin	0.11	0.11	0.13	0.14	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in TRACE report.

Output Serializer/Deserializer Switching Characteristics

Table 21: **OSERDES Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T_{OSDCK_D}/T_{OSCKD_D}	D input setup/hold with respect to CLKDIV	0.42/0.03	0.45/0.03	0.63/0.03	0.44/–0.25	ns
T_{OSDCK_T}/T_{OSCKD_T}(1)	T input setup/hold with respect to CLK	0.69/–0.13	0.73/–0.13	0.88/–0.13	0.60/–0.25	ns
$T_{OSDCK\_T2}/T_{OSCKD\_T2}$(1)	T input setup/hold with respect to CLKDIV	0.31/–0.13	0.34/–0.13	0.39/–0.13	0.46/–0.25	ns
$T_{OSCCK\_OCE}/T_{OSCKC\_OCE}$	OCE input setup/hold with respect to CLK	0.32/0.58	0.34/0.58	0.51/0.58	0.21/–0.15	ns
T_{OSCCK_S}	SR (reset) input setup with respect to CLKDIV	0.47	0.52	0.85	0.70	ns
$T_{OSCCK\_TCE}/T_{OSCKC\_TCE}$	TCE input setup/hold with respect to CLK	0.32/0.01	0.34/0.01	0.51/0.01	0.22/–0.15	ns
Sequential Delays						
T_{OSCKO_OQ}	Clock to out from CLK to OQ	0.40	0.42	0.48	0.54	ns
T_{OSCKO_TQ}	Clock to out from CLK to TQ	0.47	0.49	0.56	0.63	ns
Combinatorial						
T_{OSDO_TTQ}	T input to TQ Out	0.83	0.92	1.11	1.18	ns

Notes:

1. T_{OSDCK_T2} and T_{OSCKD_T2} are reported as T_{OSDCK_T}/T_{OSCKD_T} in TRACE report.

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 25: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{SHCKO}	Clock to A – B outputs	0.98	1.09	1.32	1.54	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs	1.37	1.53	1.86	2.18	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{DS_LRAM}/T_{DH_LRAM}	A – D inputs to CLK	0.54/0.28	0.60/0.30	0.72/0.35	0.96/0.40	ns, Min
T_{AS_LRAM}/T_{AH_LRAM}	Address An inputs to clock	0.27/0.55	0.30/0.60	0.37/0.70	0.43/0.71	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.69/0.18	0.77/0.21	0.94/0.26	1.11/0.29	ns, Min
T_{WS_LRAM}/T_{WH_LRAM}	WE input to clock	0.38/0.10	0.43/0.12	0.53/0.17	0.62/0.13	ns, Min
$T_{CECK\_LRAM}/T_{CKCE\_LRAM}$	CE input to CLK	0.39/0.10	0.44/0.11	0.53/0.17	0.63/0.12	ns, Min
Clock CLK						
T_{MPW_LRAM}	Minimum pulse width	1.05	1.13	1.25	0.82	ns, Min
T_{MCP}	Minimum clock period	2.10	2.26	2.50	1.64	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 26: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T_{REG}	Clock to A – D outputs	1.19	1.33	1.61	1.89	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output	1.58	1.77	2.15	2.53	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output	1.12	1.23	1.46	1.68	ns, Max
Setup and Hold Times Before/After Clock CLK						
$T_{WS\_SHFREG}/T_{WH\_SHFREG}$	WE input	0.37/0.10	0.41/0.12	0.51/0.17	0.59/0.13	ns, Min
$T_{CECK\_SHFREG}/T_{CKCE\_SHFREG}$	CE input to CLK	0.37/0.10	0.42/0.11	0.52/0.17	0.60/0.12	ns, Min
$T_{DS\_SHFREG}/T_{DH\_SHFREG}$	A – D inputs to CLK	0.33/0.34	0.37/0.37	0.44/0.43	0.54/0.47	ns, Min
Clock CLK						
T_{MPW_SHFREG}	Minimum pulse width	0.77	0.86	0.98	1.04	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time.

Table 27: **Block RAM and FIFO Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$T_{RCCK\_RSTRAM}/T_{RCKC\_RSTRAM}$	Synchronous RSTRAM input	0.32/0.42	0.34/0.43	0.36/0.46	0.40/0.47	ns, Min
$T_{RCCK\_WEA}/T_{RCKC\_WEA}$	Write enable (WE) input (block RAM only)	0.44/0.18	0.48/0.19	0.54/0.20	0.64/0.23	ns, Min
$T_{RCCK\_WREN}/T_{RCKC\_WREN}$	WREN FIFO inputs	0.46/0.30	0.46/0.35	0.47/0.43	0.77/0.44	ns, Min
$T_{RCCK\_RDEN}/T_{RCKC\_RDEN}$	RDEN FIFO inputs	0.42/0.30	0.43/0.35	0.43/0.43	0.71/0.44	ns, Min
Reset Delays						
T_{RCO_FLAGS}	Reset RST to FIFO flags/pointers(10)	0.90	0.98	1.10	1.25	ns, Max
$T_{RREC\_RST}/T_{RREM\_RST}$	FIFO reset recovery and removal timing(11)	1.87/–0.81	2.07/–0.81	2.37/–0.81	2.44/–0.71	ns, Max
Maximum Frequency						
$F_{MAX\_BRAM\_WF\_NC}$	Block RAM (write first and no change modes) when not in SDP RF mode	509.68	460.83	388.20	315.66	MHz
$F_{MAX\_BRAM\_RF\_PERFORMANCE}$	Block RAM (read first, performance mode) when in SDP RF mode but no address overlap between port A and port B	509.68	460.83	388.20	315.66	MHz
$F_{MAX\_BRAM\_RF\_DELAYED\_WRITE}$	Block RAM (read first, delayed write mode) when in SDP RF mode and there is possibility of overlap between port A and port B addresses	447.63	404.53	339.67	268.96	MHz
$F_{MAX\_CAS\_WF\_NC}$	Block RAM cascade (write first, no change mode) when cascade but not in RF mode	467.07	418.59	345.78	273.30	MHz
$F_{MAX\_CAS\_RF\_PERFORMANCE}$	Block RAM cascade (read first, performance mode) when in cascade with RF mode and no possibility of address overlap/one port is disabled	467.07	418.59	345.78	273.30	MHz
$F_{MAX\_CAS\_RF\_DELAYED\_WRITE}$	When in cascade RF mode and there is a possibility of address overlap between port A and port B	405.35	362.19	297.35	226.60	MHz
F_{MAX_FIFO}	FIFO in all modes without ECC	509.68	460.83	388.20	315.66	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration	410.34	365.10	297.53	215.38	MHz

Notes:

1. TRACE will report all of these parameters as T_{RCKO_DO}.
2. T_{RCKO_DOR} includes T_{RCKO_DOW}, T_{RCKO_DOPR}, and T_{RCKO_DOPW} as well as the B port equivalent timing parameters.
3. These parameters also apply to synchronous FIFO with DO_REG = 0.
4. T_{RCKO_DO} includes T_{RCKO_DOP} as well as the B port equivalent timing parameters.
5. These parameters also apply to multirate (asynchronous) and synchronous FIFO with DO_REG = 1.
6. T_{RCKO_FLAGS} includes the following parameters: T_{RCKO_AEMPTY}, T_{RCKO_AFULL}, T_{RCKO_EMPTY}, T_{RCKO_FULL}, T_{RCKO_RDERR}, T_{RCKO_WRERR}.
7. $T_{RCKO\_POINTERS}$ includes both $T_{RCKO\_RDCOUNT}$ and $T_{RCKO\_WRCOUNT}$.
8. The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
9. These parameters include both A and B inputs as well as the parity inputs of A and B.
10. T_{RCO_FLAGS} includes the following flags: AEMPTY, AFULL, EMPTY, FULL, RDERR, WRERR, RDCOUNT, and WRCOUNT.
11. RDEN and WREN must be held Low prior to and during reset. The FIFO reset must be asserted for at least five positive clock edges of the slowest clock (WRCLK or RDCLK).

DSP48E1 Switching Characteristics

Table 28: **DSP48E1 Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Setup and Hold Times of Data/Control Pins to the Input Register Clock						
$T_{DSPDCK\_A\_AREG}$/ $T_{DSPCKD\_A\_AREG}$	A input to A register CLK	0.26/ 0.12	0.30/ 0.13	0.37/ 0.14	0.45/ 0.14	ns
$T_{DSPDCK\_B\_BREG}$/$T_{DSPCKD\_B\_BREG}$	B input to B register CLK	0.33/ 0.15	0.38/ 0.16	0.45/ 0.18	0.60/ 0.19	ns
$T_{DSPDCK\_C\_CREG}$/$T_{DSPCKD\_C\_CREG}$	C input to C register CLK	0.17/ 0.17	0.20/ 0.19	0.24/ 0.21	0.34/ 0.29	ns
$T_{DSPDCK\_D\_DREG}$/$T_{DSPCKD\_D\_DREG}$	D input to D register CLK	0.25/ 0.25	0.32/ 0.27	0.42/ 0.27	0.54/ 0.23	ns
$T_{DSPDCK\_ACIN\_AREG}$/$T_{DSPCKD\_ACIN\_AREG}$	ACIN input to A register CLK	0.23/ 0.12	0.27/ 0.13	0.32/ 0.14	0.36/ 0.14	ns
$T_{DSPDCK\_BCIN\_BREG}$/$T_{DSPCKD\_BCIN\_BREG}$	BCIN input to B register CLK	0.25/ 0.15	0.29/ 0.16	0.36/ 0.18	0.41/ 0.19	ns
Setup and Hold Times of Data Pins to the Pipeline Register Clock						
$T_{DSPDCK\_\{A, B\}\_MREG\_MULT}$/ $T_{DSPCKD\_B\_MREG\_MULT}$	{A, B} input to M register CLK using multiplier	2.40/ –0.01	2.76/ –0.01	3.29/ –0.01	4.31/ –0.07	ns
$T_{DSPDCK\_\{A, B\}\_ADREG}$/ $T_{DSPCKD\_ D\_ADREG}$	{A, D} input to AD register CLK	1.29/ –0.02	1.48/ –0.02	1.76/ –0.02	2.29/ –0.27	ns
Setup and Hold Times of Data/Control Pins to the Output Register Clock						
$T_{DSPDCK\_\{A, B\}\_PREG\_MULT}$/ $T_{DSPCKD\_\{A, B\} \_PREG\_MULT}$	{A, B} input to P register CLK using multiplier	4.02/ –0.28	4.60/ –0.28	5.48/ –0.28	6.95/ –0.48	ns
$T_{DSPDCK\_D\_PREG\_MULT}$/ $T_{DSPCKD\_D\_PREG\_MULT}$	D input to P register CLK using multiplier	3.93/ –0.73	4.50/ –0.73	5.35/ –0.73	6.73/ –1.68	ns
$T_{DSPDCK\_\{A, B\} \_PREG}$/ $T_{DSPCKD\_\{A, B\} \_PREG}$	A or B input to P register CLK not using multiplier	1.73/ –0.28	1.98/ –0.28	2.35/ –0.28	2.80/ –0.48	ns
$T_{DSPDCK\_C\_PREG}$/ $T_{DSPCKD\_C\_PREG}$	C input to P register CLK not using multiplier	1.54/ –0.26	1.76/ –0.26	2.10/ –0.26	2.54/ –0.45	ns
$T_{DSPDCK\_PCIN\_PREG}$/ $T_{DSPCKD\_PCIN\_PREG}$	PCIN input to P register CLK	1.32/ –0.15	1.51/ –0.15	1.80/ –0.15	2.13/ –0.25	ns
Setup and Hold Times of the CE Pins						
$T_{DSPDCK\_\{CEA;CEB\}\_\{AREG;BREG\}}$/ $T_{DSPCKD\_\{CEA;CEB\}\_\{AREG;BREG\}}$	{CEA; CEB} input to {A; B} register CLK	0.35/ 0.06	0.42/ 0.08	0.52/ 0.11	0.64/ 0.11	ns
$T_{DSPDCK\_CEC\_CREG}$/ $T_{DSPCKD\_CEC\_CREG}$	CEC input to C register CLK	0.28/ 0.10	0.34/ 0.11	0.42/ 0.13	0.49/ 0.16	ns
$T_{DSPDCK\_CED\_DREG}$/ $T_{DSPCKD\_CED\_DREG}$	CED input to D register CLK	0.36/ –0.03	0.43/ –0.03	0.52/ –0.03	0.68/ 0.14	ns
$T_{DSPDCK\_CEM\_MREG}$/ $T_{DSPCKD\_CEM\_MREG}$	CEM input to M register CLK	0.17/ 0.18	0.21/ 0.20	0.27/ 0.23	0.45/ 0.29	ns
$T_{DSPDCK\_CEP\_PREG}$/ $T_{DSPCKD\_CEP\_PREG}$	CEP input to P register CLK	0.36/ 0.01	0.43/ 0.01	0.53/ 0.01	0.63/ 0.00	ns

Table 32: **Horizontal Clock Buffer Switching Characteristics (BUFH)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BHCKO_O}	BUFH delay from I to O	0.10	0.11	0.13	0.16	ns
$T_{BHCCK\_CE}/T_{BHCKC\_CE}$	CE pin setup and hold	0.19/0.13	0.22/0.15	0.28/0.21	0.35/0.08	ns
Maximum Frequency						
F_{MAX_BUFH}	Horizontal clock buffer (BUFH)	628.00	628.00	464.00	394.00	MHz

Table 33: **Duty Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
T_{DCD_CLK}	Global clock tree duty-cycle distortion(1)	All	0.20	0.20	0.20	0.25	ns
T_{CKSKEW}	Global clock tree skew(2)	XC7A100T	0.27	0.33	0.36	0.48	ns
		XC7A200T	0.40	0.48	0.54	0.69	ns
T_{DCD_BUFIO}	I/O clock tree duty cycle distortion	All	0.14	0.14	0.14	0.14	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region	All	0.03	0.03	0.03	0.03	ns
T_{DCD_BUFR}	Regional clock tree duty cycle distortion	All	0.18	0.18	0.18	0.18	ns

Notes:

1. These parameters represent the worst-case duty cycle distortion observable at the I/O flip flops. For all I/O standards, IBIS can be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx FPGA_Editor and Timing Analyzer tools to evaluate clock skew specific to your application.

MMCM Switching Characteristics

Table 34: **MMCM Specification**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
MMCM_F_{INMAX}	Maximum input clock frequency	800.00	800.00	800.00	800.00	MHz
MMCM_F_{INMIN}	Minimum input clock frequency	10.00	10.00	10.00	10.00	MHz
MMCM_$F_{INJITTER}$	Maximum input clock period jitter	< 20% of clock input period or 1 ns Max				
MMCM_F_{INDUTY}	Allowable input duty cycle: 10—49 MHz	25	25	25	25	%
	Allowable input duty cycle: 50—199 MHz	30	30	30	30	%
	Allowable input duty cycle: 200—399 MHz	35	35	35	35	%
	Allowable input duty cycle: 400—499 MHz	40	40	40	40	%
	Allowable input duty cycle: >500 MHz	45	45	45	45	%
MMCM_F_{MIN_PSCLK}	Minimum dynamic phase-shift clock frequency	0.01	0.01	0.01	0.01	MHz
MMCM_F_{MAX_PSCLK}	Maximum dynamic phase-shift clock frequency	550.00	500.00	450.00	450.00	MHz
MMCM_F_{VCOMIN}	Minimum MMCM VCO frequency	600.00	600.00	600.00	600.00	MHz
MMCM_F_{VCOMAX}	Maximum MMCM VCO frequency	1600.00	1440.00	1200.00	1200.00	MHz

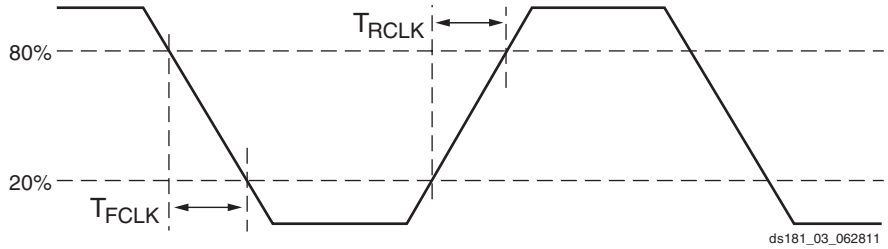

Figure 3: **Reference Clock Timing Parameters**

Table 52: **GTP Transceiver PLL/Lock Time Adaptation**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
T_{LOCK}	Initial PLL lock		–	–	1	ms
T_{DLOCK}	Clock recovery phase acquisition and adaptation time.	After the PLL is locked to the reference clock, this is the time it takes to lock the clock data recovery (CDR) to the data present at the input.	–	50,000	2.3×10^6	UI

Table 53: **GTP Transceiver User Clock Switching Characteristics(1)**

Symbol	Description	Conditions	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
F_{TXOUT}	TXOUTCLK maximum frequency		412.500	412.500	234.375	234.375	MHz
F_{RXOUT}	RXOUTCLK maximum frequency		412.500	412.500	234.375	234.375	MHz
F_{TXIN}	TXUSRCLK maximum frequency	16-bit data path	412.500	412.500	234.375	234.375	MHz
F_{RXIN}	RXUSRCLK maximum frequency	16-bit data path	412.500	412.500	234.375	234.375	MHz
F_{TXIN2}	TXUSRCLK2 maximum frequency	16-bit data path	412.500	412.500	234.375	234.375	MHz
F_{RXIN2}	RXUSRCLK2 maximum frequency	16-bit data path	412.500	412.500	234.375	234.375	MHz

Notes:

1. Clocking must be implemented as described in UG482: *7 Series FPGAs GTP Transceiver User Guide*.

Table 55: **GTP Transceiver Receiver Switching Characteristics**

Symbol	Description		Min	Typ	Max	Units
F_{GTPRX}	Serial data rate	RX oversampler not enabled	0.500	–	F_{GTPMAX}	Gb/s
$T_{RXELECIDLE}$	Time for RXELECIDLE to respond to loss or restoration of data		–	10	–	ns
$RX_{OOBVDPP}$	OOB detect threshold peak-to-peak		60	–	150	mV
RX_{SST}	Receiver spread-spectrum tracking(1)	Modulated @ 33 KHz	–5000	–	5000	ppm
RX_{RL}	Run length (CID)		–	–	512	UI
RX_{PPMTOL}	Data/REFCLK PPM offset tolerance		–1250	–	1250	ppm
SJ Jitter Tolerance(2)						
$JT\_SJ_{6.6}$	Sinusoidal Jitter(3)	6.6 Gb/s	0.44	–	–	UI
$JT\_SJ_{5.0}$	Sinusoidal Jitter(3)	5.0 Gb/s	0.44	–	–	UI
$JT\_SJ_{4.25}$	Sinusoidal Jitter(3)	4.25 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.75}$	Sinusoidal Jitter(3)	3.75 Gb/s	0.44	–	–	UI
$JT\_SJ_{3.2}$	Sinusoidal Jitter(3)	3.2 Gb/s(4)	0.45	–	–	UI
$JT\_SJ_{3.2L}$	Sinusoidal Jitter(3)	3.2 Gb/s(5)	0.45	–	–	UI
$JT\_SJ_{2.5}$	Sinusoidal Jitter(3)	2.5 Gb/s(6)	0.5	–	–	UI
$JT\_SJ_{1.25}$	Sinusoidal Jitter(3)	1.25 Gb/s(7)	0.5	–	–	UI
JT_SJ_{500}	Sinusoidal Jitter(3)	500 Mb/s	0.4	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$JT\_TJSE_{3.2}$	Total Jitter with Stressed Eye(8)	3.2 Gb/s	0.70	–	–	UI
$JT\_TJSE_{6.6}$		6.6 Gb/s	0.70	–	–	UI
$JT\_SJSE_{3.2}$	Sinusoidal Jitter with Stressed Eye(8)	3.2 Gb/s	0.1	–	–	UI
$JT\_SJSE_{6.6}$		6.6 Gb/s	0.1	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of $1e^{-12}$.
3. The frequency of the injected sinusoidal jitter is 10 MHz.
4. PLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. PLL frequency at 1.6 GHz and RXOUT_DIV = 1.
6. PLL frequency at 2.5 GHz and RXOUT_DIV = 2.
7. PLL frequency at 2.5 GHz and RXOUT_DIV = 4.
8. Composite jitter.

GTP Transceiver Protocol Jitter Characteristics

For Table 56 through Table 60, the UG482: *7 Series FPGAs GTP Transceiver User Guide* contains recommended settings for optimal usage of protocol specific characteristics.

Table 56: **Gigabit Ethernet Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
Gigabit Ethernet Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	1250	–	0.24	UI
Gigabit Ethernet Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	1250	0.749	–	UI

Table 57: **XAUI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
XAUI Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	3125	–	0.35	UI
XAUI Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	3125	0.65	–	UI

Table 58: **PCI Express Protocol Characteristics(1)**

Standard	Description	Line Rate (Mb/s)	Min	Max	Units
PCI Express Transmitter Jitter Generation					
PCI Express Gen 1	Total transmitter jitter	2500	–	0.25	UI
PCI Express Gen 2	Total transmitter jitter	5000	–	0.25	UI
PCI Express Receiver High Frequency Jitter Tolerance					
PCI Express Gen 1	Total receiver jitter tolerance	2500	0.65	–	UI
PCI Express Gen 2(2)	Receiver inherent timing error	5000	0.40	–	UI
	Receiver inherent deterministic timing error		0.30	–	UI

Notes:

1. Tested per card electromechanical (CEM) methodology.
2. Using common REFCLK.

Table 59: **CEI-6G Protocol Characteristics**

Description	Line Rate (Mb/s)	Interface	Min	Max	Units
CEI-6G Transmitter Jitter Generation					
Total transmitter jitter(1)	4976–6375	CEI-6G-SR	–	0.3	UI
CEI-6G Receiver High Frequency Jitter Tolerance					
Total receiver jitter tolerance(1)	4976–6375	CEI-6G-SR	0.6	–	UI

Notes:

1. Tested at most commonly used line rate of 6250 Mb/s using 390.625 MHz reference clock.

Table 63: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Internal Configuration Access Port						
F_{ICAPCK}	Internal configuration access port (ICAPE2) clock frequency	100.00	100.00	100.00	70.00	MHz, Max
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{CCO}	DOUT clock to out	8.00	8.00	8.00	9.00	ns, Max
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	D[31:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{SMWCCK}/T_{SMCCKW}	RDWR_B setup/hold	10.00/0.00	10.00/0.00	10.00/0.00	12.00/0.00	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	7.00	7.00	7.00	8.00	ns, Max
T_{SMCO}	D[31:00] clock to out in readback	8.00	8.00	8.00	10.00	ns, Max
F_{RBCCK}	Readback frequency	100.00	100.00	100.00	70.00	MHz, Max
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup/hold	3.00/2.00	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	8.50	ns, Max
F_{TCK}	TCK frequency	66.00	66.00	66.00	50.00	MHz, Max
BPI Flash Master Mode Programming Switching						
T_{BPICCO} (2)	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out	8.50	8.50	8.50	10.00	ns, Max
T_{BPIDCC}/T_{BPICCD}	D[15:00] setup/hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
SPI Flash Master Mode Programming Switching						
T_{SPIDCC}/T_{SPICCD}	D[03:00] setup/hold	3.00/0.00	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T_{SPICCM}	MOSI clock to out	8.00	8.00	8.00	9.00	ns, Max
$T_{SPICCFC}$	FCS_B clock to out	8.00	8.00	8.00	9.00	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in UG470: *7 Series FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 64 lists the programming conditions specifically for eFUSE. For more information, see UG470: *7 Series FPGA Configuration User Guide*.

Table 64: **eFUSE Programming Conditions** (1)

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

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